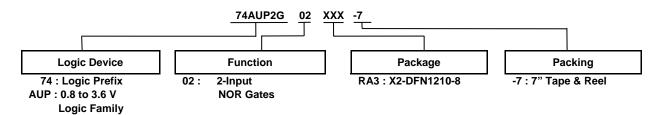


Ordering Information

2G : Dual Gate



7" Tape and Reel Package **Package Package** Device Part Number Code (Notes 4 & 5) Size Quantity Suffix 1.2mm X 1.0mm X 0.35mm 74AUP2G02RA3-7 RA3 X2-DFN1210-8 5,000/Tape & Reel -7

0.3 mm lead pitch

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Pin Descriptions

Pin Name	Pin No.	Function
1A	1	Data Input
1B	2	Data Input
2Y	3	Data Output
GND	4	Ground
2A	5	Data Input
2B	6	Data Input
1Y	7	Data Output
V _{CC}	8	Supply Voltage

Logic Diagram

Function Table

Inp	Inputs					
Α	A B					
L	L	Н				
L	Н	L				
Н	L	L				
Н	Н	L				



Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	50	mA
lok	Output Clamp Current (V _O < 0)	50	mA
Io	Continuous Output Current (V _O = 0 to V _{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes:

Recommended Operating Conditions (Note 8)

Symbol	Pa	arameter	Min	Max	Unit
Vcc	Operating Voltage	_	0.8	3.6	V
Vı	Input Voltage	1	0	3.6	V
Vo	Output Voltage		0	V _{CC}	V
		V _{CC} = 0.8V	_	-20	μΑ
		V _{CC} = 1.1V	_	-1.1	
	High Lavel Outrat Outrat	V _{CC} = 1.4V	_	-1.7	
I _{OH}	High-Level Output Current	V _{CC} = 1.65V	_	-1.9	mA
		V _{CC} = 2.3V	_	-3.1	
		V _{CC} = 3.0V	_	-4	
		V _{CC} = 0.8V	_	20	μA
		V _{CC} = 1.1V	_	1.1	
		V _{CC} = 1.4V	_	1.7	
I _{OL}	Low-Level Output Current	V _{CC} = 1.65V	_	1.9	mA
		V _{CC} = 2.3V	_	3.1	
		V _{CC} = 3.0V	_	— 4	
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 0.8V to 3.6V	_	200	ns/V
T _A	Operating Free-Air Temperature	_	-40	+125	°C

Note: 8. Unused inputs should be held at V_{CC} or Ground.

^{6.} Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device

operation should be within recommend values.

7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



Electrical Characteristics

Symbol	Parameter	Test Conditions	V	T _A = -	+25°C	T _A = -40°0	C to +85°C	Unit
Symbol	Parameter	rest Conditions	V _{CC}	Min	Max	Min	Max	Unit
		_	0.8V to 1.65V	0.80 X V _{CC}	_	0.80 X V _{CC}	_	
V _{IH}	High-Level Input	_	1.65V to 1.95V	0.65 X V _{CC}	_	0.65 X V _{CC}	_	V
VIH	Voltage	1	2.3V to 2.7V	1.6	_	1.6	_	v
			3.0V to 3.6V	2.0	_	2.0	_	
		1	0.8V to 1.65V	_	0.30 X V _{CC}	_	0.30 X V _{CC}	
V _{IL}	Low-Level Input	1	1.65V to 1.95V	_	0.35 X V _{CC}	_	0.35 X V _{CC}	V
V IL	Voltage	1	2.3V to 2.7V	_	0.7	_	0.7]
			3.0V to 3.6V		0.9		0.9	
		I _{OH} = -20μA	0.8V to 3.6V	V _{CC} – 0.1	_	V _{CC} – 0.1	_	
		I_{OH} = -1.1mA	1.1V	0.75 X V _{CC}	_	0.7 X V _{CC}	_	
		$I_{OH} = -1.7 \text{mA}$	1.4V	1.11	_	1.03	_	
.,	High-Level Output	I _{OH} = -1.9mA	1.65V	1.32	_	1.3	_	V
VoH	Voltage	I _{OH} = -2.3mA	2.21/	2.05	_	1.97	_	
		I _{OH} = -3.1mA	2.3V	1.9	_	1.85	_	
		I _{OH} = -2.7mA	- 3V	2.72	_	2.67	_	
		I _{OH} = -4mA	30	2.6	_	2.55	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.1	_	0.1	
		I _{OL} = 1.1mA	1.1V	_	0.3 X V _{CC}	_	0.3 X V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.31	_	0.37	
.,	Low-Level Input	I _{OL} = 1.9mA	1.65V	_	0.31	_	0.35	.,
Vol	Voltage	I _{OL} = 2.3mA	0.01/	_	0.31	_	0.33	V
		I _{OL} = 3.1mA	2.3V	_	0.44	_	0.45	
		I _{OL} = 2.7mA	0) /	_	0.31	_	0.33	
		I _{OL} = 4mA	3V	_	0.44	_	0.45	
II	Input Current	A or B Input V _I = GND to 3.6V	0V to 3.6V	_	± 0.1	_	± 0.5	μΑ
I _{OFF}	Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0V	_	± 0.2	_	± 0.6	μΑ
Δl _{OFF}	Delta Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	± 0.2	_	± 0.6	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	0.5	_	0.9	μA
ΔI _{CC}	Additional Supply Current	One Input at V _{CC} –0.6V Other Inputs at V _{CC} or GND	3.3V	_	40	_	50	μA



Electrical Characteristics (continued)

Symbol	Parameter	Test Conditions	V	T _A = -40°C	to +125°C	Unit
Symbol	Parameter	rest Conditions	V _{CC}	Min	Max	Unit
		_	0.8V to 1.65V	0.80 X V _{CC}	_	
V _{IH}	High-Level Input Voltage	_	1.65V to 1.95V	0.70 X V _{CC}	_	V
VIH	Triigh-Level input voltage	_	2.3V to 2.7V	1.6	_	v
		_	3.0V to 3.6V	2.0	_	
		_	0.8V to 1.65V	_	0.25 X V _{CC}	
V_{IL}	Low-Level Input Voltage	_	1.65V to 1.95V		0.30 X V _{CC}	V
VIL	Low Level input voltage	_	2.3V to 2.7V	_	0.7	·
		_	3.0V to 3.6V		0.9	
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V _{CC} – 0.11	_	
		$I_{OH} = -1.1$ mA	1.1V	0.6 X V _{CC}	_	
		I _{OH} = -1.7mA	1.4V	0.93	_	
	High Lavel Output Valters	I _{OH} = -1.9mA	1.65V	1.17	_	.,
Vон	High-Level Output Voltage	I _{OH} = -2.3mA	2.21/	1.77	_	V
		I _{OH} = -3.1mA	2.3V	1.67	_	
		I _{OH} = -2.7mA	21/	2.40	_	
		I _{OH} = -4mA	3V	2.30	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.11	
		I _{OL} = 1.1mA	1.1V	_	0.33 X V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.41	
.,	Lava Lava Harrist Walterna	I _{OL} = 1.9mA	1.65V	_	0.39	.,
V _{OL}	Low-Level Input Voltage	I _{OL} = 2.3mA	0.01/	_	0.36	V
		I _{OL} = 3.1mA	2.3V	_	0.50	
		I _{OL} = 2.7mA	01/	_	0.36	
		I _{OL} = 4mA	3V	_	0.50	
l _l	Input Current	A or B Input, V _I = GND to 3.6V	0V to 3.6V	_	± 0.75	μA
l _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V	_	± 1.0	μA
Δl _{OFF}	Delta Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	3.0	μA
Δl _{CC}	Additional Supply Current	Input at V _{CC} –0.6V Other Inputs at V _{CC} or GND	3.3V	_	75	μΑ

Operating and Package Characteristics (@T_A = +25°C, unless otherwise specified.)

	Parameter	Tes Condi		V _{CC}	Тур	Unit
				0.8V	5.1	
				1.2V ± 0.1V	5.2	
	Power Dissipation	f = 1N	ИHz	1.5V ± 0.1V	5.2	T
C_{pd}	Capacitance	No Lo	oad	1.8V ± 0.15V	5.5	pF
				2.5V ± 0.2V	5.7	1
				3.3V ± 0.3V	6.0	
C _i	Input Capacitance	$V_i = V_{CC}$	or GND	0V or 3.3V	2.0	pF
θ _{JA}	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8	(Note 9)	_	+395	°C/W
θ _{JC}	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	_	+236	°C/W

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Switching Characteristics

C_L = 5pF, See Figure 1

Parameter	From	То	V _{CC}		T _A = +25°C	;	$T_A = -40^{\circ}C$	c to +85°C	T _A = -40°C	to +125°C	Unit
r arameter	Input	Output	VCC	Min	Тур	Max	Min	Max	Min	Max	Oiiit
			V8.0	_	19.6	_	_	_	_	_	
			1.2V ± 0.1V	2.5	5.1	11.9	2.1	13.3	2.1	14.7	ns
	A or D	_	1.5V ± 0.1V	1.6	3.7	6.7	1.4	7.8	1.4	8.6	
t _{pd}	A or B	Y	1.8V ± 0.15V	1.3	3.0	5.3	1.1	6.2	1.1	6.9	
			2.5V ± 0.2V	1.0	2.4	3.9	0.9	4.6	0.9	5.1	
			3.3V ± 0.3V	1.0	2.2	3.4	0.8	4.0	8.0	4.4	

C_L = 10pF, See Figure 1

Parameter	From	То	V		T _A = +25°C	;	T _A = -40°C	C to +85°C	T _A = -40°C	Unit	
Faranietei	Input Output		V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Ullit
		3 Y	0.8V	_	23.5	_	_	_	_	_	
			1.2V ± 0.1V	2.4	6.0	14.1	2.2	15.7	2.2	17.4	- ns
	A or B		1.5V ± 0.1V	1.9	4.3	7.9	1.7	9.2	1.7	10.2	
t _{pd}	AUID		1.8V ± 0.15V	1.6	3.6	6.2	1.5	7.3	1.5	8.1	
			2.5V ± 0.2V	1.4	3.0	4.7	1.2	5.6	1.2	6.2	
			$3.3V \pm 0.3V$	1.3	2.7	4.2	1.2	5.0	1.2	5.5	

C_L = 15pF, See Figure 1

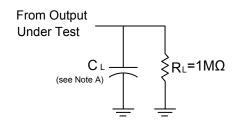
Parameter	From To		V	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
Farameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Ollit
			V8.0	_	27.5	_	_	_	_	_	
			1.2V ± 0.1V	3.4	6.8	16.1	3.1	20.2	3.1	20.4	ns
	A or D	_	1.5V ± 0.1V	2.3	4.8	8.9	2.0	10.4	2.0	11.5	
t _{pd}	A or B	T	1.8V ± 0.15V	1.9	4.0	7.0	1.7	8.3	1.7	9.2	
			2.5V ± 0.2V	1.7	3.4	5.4	1.5	6.3	1.5	7.0	
			3.3V ± 0.3V	1.4	3.2	4.8	1.3	5.7	1.3	6.3	

C_L = 30pF, See Figure 1

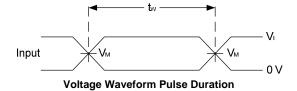
Parameter	From	То	V		T _A = +25°C	;	$T_A = -40^{\circ}C$	to +85°C	T _A = -40°C	to +125°C	Unit
rarameter	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Ollit
			0.8V	_	39.3	_	_	_	_	_	ns
			1.2V ± 0.1V	4.6	9.0	21.9	4.1	27.6	4.1	27.8	
	A or B	_	1.5V ± 0.1V	3.4	6.4	11.8	2.9	13.9	2.9	15.3	
τ _{pd}	d A or B Y	I	1.8V ± 0.15V	2.6	5.3	9.3	2.3	11.1	2.3	12.3	
			2.5V ± 0.2V	2.4	4.5	7.1	2.1	8.5	2.1	9.4	
			3.3V ± 0.3V	2.0	4.2	6.4	1.8	7.7	1.8	8.5	

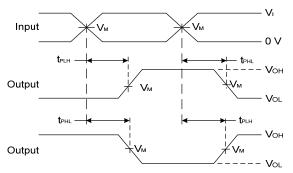


Parameter Measurement Information



V	In	puts	V.	
Vcc	VI	t _r /t _f	V _M	CL
0.8V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.2V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.5V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.8V ± 0.15V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
2.5V ± 0.2V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
3.3V ± 0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF





Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
 C. Inputs are measured separately one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$



Marking Information

X2-DFN1210-8

(Top View)

 $\underline{\mathsf{XX}}$: Identification Code

Y : Year : 0~9

 $\overline{\underline{W}}$: week: A~Z: 1~26 week

a~z: 27-52 week

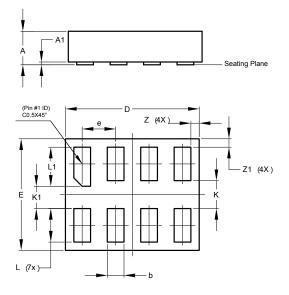
z represents 52 and 53 week

 \underline{X} : week: A~Z: Internal code

Part Number	Package	Identification Code
74AUP2G02RA3-7	X2-DFN1210-8	ВТ

X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



		-		— X1		-	
	<u> </u>						_
Y1	G —						
	_		c	_ · ~ —	<u> </u>	×	

X2-DFN1210-8						
Dim	Min	Max	Тур			
Α	-	0.35	0.30			
A 1	0	0.03	0.02			
b	0.10	0.20	0.15			
D	1.15	1.25	1.20			
Е	0.95	1.05	1.00			
е	-	-	0.30			
K	-	-	0.25			
K1	-	-	0.20			
L	0.25	0.35	0.30			
L1	0.30	0.40	0.35			
Z	0.050	0.100	0.075			
Z 1	0.050	0.100	0.075			
All Dimensions in mm						

Dimensions	Value (in mm)
С	0.300
G	0.150
Х	0.150
X1	1.050
Y	0.500
Y1	1.150



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